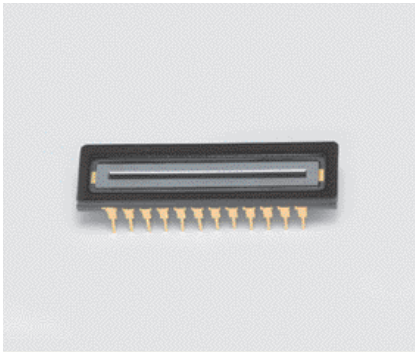


# CCD linear image sensors

S11155-2048 S11156-2048



## Back-thinned CCD image sensors with electronic shutter function

The S11155-2048 and S11156-2048 are back-thinned CCD linear image sensors with an internal electronic shutter for spectrometers. These image sensors use a resistive gate structure that allows high-speed transfer. Each pixel has a lengthwise size needed by spectrometers but ensures readout with low image lag.

### Features

- ➔ **Built-in electronic shutter**
- ➔ **Minimum integration time: 30 μs**
- ➔ **High sensitivity from the ultraviolet region (spectral response range: 200 to 1100 nm)**
- ➔ **Readout speed: 10 MHz max.**
- ➔ **Image lag: 0.1% typ.**

### Applications

- ➔ **Spectrometers**
- ➔ **Image readout**

### General ratings

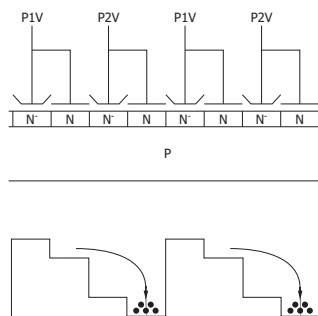
Parameter	S11155-2048	S11156-2048
Pixel size	14 (H) × 500 (V) μm	14 (H) × 1000 (V) μm
Number of total pixels	2068 (H) × 1 (V)	
Number of active pixels	2048 (H) × 1 (V)	
Active area	28.672 (H) × 0.500 (V) mm	28.672 (H) × 1.000 (V) mm
Horizontal clock phase	2-phase	
Output circuit	Two-stage MOSFET source follower	
Package	24-pin ceramic DIP (refer to dimensional outline)	
Window*1	Quartz glass	

\*1: Temporary window type (ex. S11155-2048N) is available upon request.

### Resistive gate structure

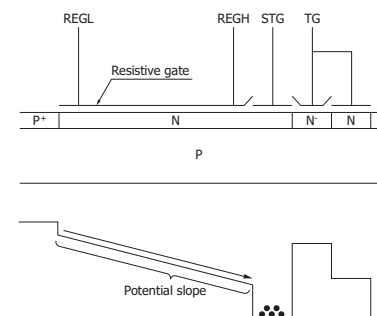
In ordinary CCDs, one pixel contains multiple electrodes and a signal charge is transferred by applying different clock pulses to those electrodes [Figure 1]. In resistive gate structures, a single high-resistance electrode is formed in the active area, and a signal charge is transferred by means of a potential slope that is created by applying different voltages across the electrode [Figure 2]. Compared to a CCD area image sensor which is used as a linear sensor by line binning, a one-dimensional CCD having a resistive gate structure in the active area offers higher speed transfer, allowing readout with low image lag even if the pixel height is large.

[Figure 1] Schematic diagram and potential of ordinary 2-phase CCD



KMPDC0320EA

[Figure 2] Schematic diagram and potential of resistive gate structure



KMPDC0321EB

**▣ Absolute maximum ratings (Ta=25 °C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Operating temperature*2 *3	Topr	-50	-	+50	°C	
Storage temperature	Tstg	-50	-	+70	°C	
OD voltage	VOD	-0.5	-	+25	V	
RD voltage	VRD	-0.5	-	+18	V	
Vret voltage	Vret	-0.5	-	+18	V	
ARD voltage	VARD	-0.5	-	+18	V	
ISH voltage	VISH	-0.5	-	+18	V	
ARG voltage	VARG	-10	-	+15	V	
STG voltage	VSTG	-10	-	+15	V	
IGH voltage	VIG1H, VIG2H	-10	-	+15	V	
SG voltage	VSG	-10	-	+15	V	
OG voltage	VOG	-10	-	+15	V	
RG voltage	VRG	-10	-	+15	V	
TG voltage	VTG	-10	-	+15	V	
Resistive gate voltage	High	VREGH	-10	-	+15	V
	Low	VREGL				
Horizontal clock voltage	VP1H, VP2H	-10	-	+15	V	

\*2: Chip temperature

\*3: The chip temperature may increase due to heating in high-speed operation. We recommend taking measures to dissipate heat as needed. For more details, refer to the technical information.

**▣ Operating conditions (Ta=25 °C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Output transistor drain voltage	VOD	12	15	18	V	
Reset drain voltage	VRD	14	15	16	V	
All reset drain voltage	VARD	11	12	13	V	
All reset gate voltage	High*4	VARGH	7	8	9	V
	Low*5	VARGL	-2	-1.5	-1	
Output gate voltage	VOG	4.5	5	5.5	V	
Storage gate voltage	VSTG	-	0	-	V	
Substrate voltage	VSS	-	0	-	V	
Resistive gate high voltage	High	VREGHH	-3.5	-3	-2.5	V
	Low	VREGHL	-9	-8	-7	
Resistive gate low voltage	High	VREGLH	-	VREGHH - 2.5	-	V
	Low	VREGLL	-9	-8	-7	
Output amplifier return voltage	Vret	-	1	2	V	
Test point	Horizontal input source	VISH	-	VRD	-	V
	Horizontal input gate	VIG1H, VIG2H	-9	-8	-	V
Horizontal shift register clock voltage	High	VP1HH, VP2HH	5	6	7	V
	Low	VP1HL, VP2HL	-6	-5	-4	
Summing gate voltage	High	VSGH	5	6	7	V
	Low	VSGL	-6	-5	-4	
Reset gate voltage	High	VRGH	7	8	9	V
	Low	VRGL	-6	-5	-4	
Transfer gate voltage	High	VTGH	8.5	9	9.5	V
	Low	VTGL	-7.5	-7	-6.5	
External load resistance	RL	2.0	2.2	2.4	kΩ	

\*4: All reset on

\*5: All reset off

**Electrical characteristics (Ta=25 °C)**

Parameter		Symbol	Min.	Typ.	Max.	Unit
Signal output frequency		fc	-	5	10	MHz
Line rate		LR	-	2	4	kHz
Horizontal shift register capacitance		CP1H, CP2H	-	200	-	pF
All reset gate capacitance		CARG	-	100	-	pF
Resistive gate capacitance	S11155-2048	CREG	-	1000	-	pF
	S11156-2048		-	2000	-	
Summing gate capacitance		CSG	-	10	-	pF
Reset gate capacitance		CRG	-	10	-	pF
Transfer gate capacitance		CTG	-	100	-	pF
Charge transfer efficiency*6		CTE	0.99995	0.99999	-	-
DC output level		Vout	7	8	9	V
Output impedance		Zo	-	300	-	Ω
Output amplifier return current		Iret	-	0.4	-	mA
Power consumption	S11155-2048	PAMP*7	-	75	-	mW
		PREG*8	1.4	2.5	12.5	
	S11156-2048	PAMP*7	-	75	-	
		PREG*8	0.7	1.3	6.3	
Resistive gate resistance*9	S11155-2048	RREG	0.5	2.5	4.5	kΩ
	S11156-2048		1	5	9	

\*6: Charge transfer efficiency per pixel of CCD shift register, measured at half of the full well capacity

\*7: Power consumption of the on-chip amplifier plus load resistance

\*8: Power consumption at REG

\*9: Resistance value between REGH and REGL

**Electrical and optical characteristics (Ta=25 °C, unless otherwise noted)**

Parameter	Symbol	S11155-2048			S11156-2048			Unit	
		Min.	Typ.	Max.	Min.	Typ.	Max.		
Saturation output voltage	Vsat	-	Fw x Sv	-	-	Fw x Sv	-	V	
Full well capacity	Fw	-	200	-	-	200	-	ke <sup>-</sup>	
CCD node sensitivity	Sv	7	8	9	7	8	9	μV/e <sup>-</sup>	
Dark current*10	Non-MPP operation	DS	-	50	300	-	100	600	ke <sup>-</sup> /pixel/s
	MPP operation		-	4	16	-	8	32	
Readout noise*11	Nr	-	30	45	-	30	45	e <sup>-</sup> rms	
Dynamic range*12	DR	-	6670	-	-	6670	-	-	
Spectral response range	λ	-	200 to 1100	-	-	200 to 1100	-	nm	
Photo response non-uniformity*13, *14	PRNU	-	±3	±10	-	±3	±10	%	
Image lag*13	L	-	0.1	1	-	0.1	1	%	

\*10: Dark current is reduced to half for every 5 to 7 °C decrease in temperature.

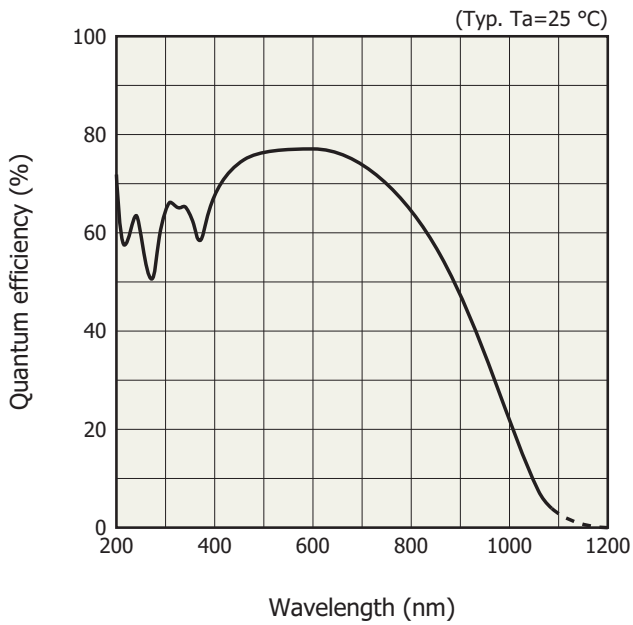
\*11: Readout frequency is 2 MHz

\*12: Dynamic range (DR) = Full well capacity / Readout noise

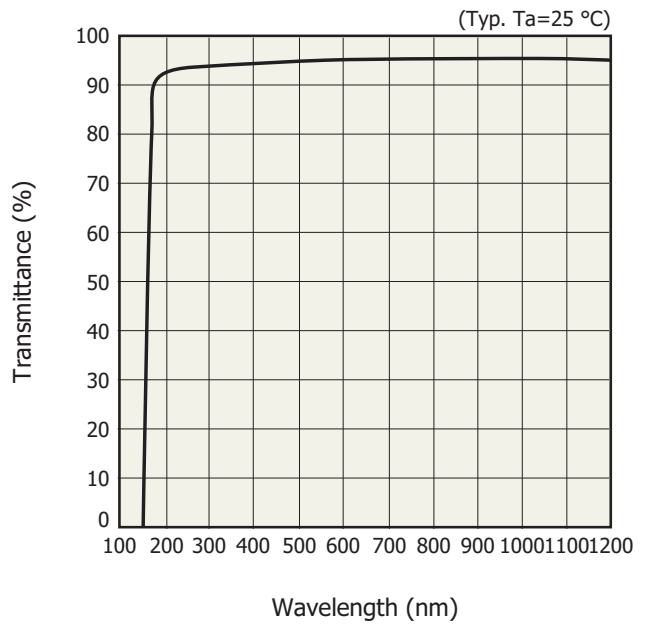
\*13: Measured at one-half of the saturation output (full well capacity) using LED light (peak emission wavelength: 660 nm)

\*14: Photo response non-uniformity =  $\frac{\text{Fixed pattern noise (peak to peak)}}{\text{Signal}} \times 100$  [%]

**Spectral response (without window)\*15**



**Spectral transmittance characteristic of window material**



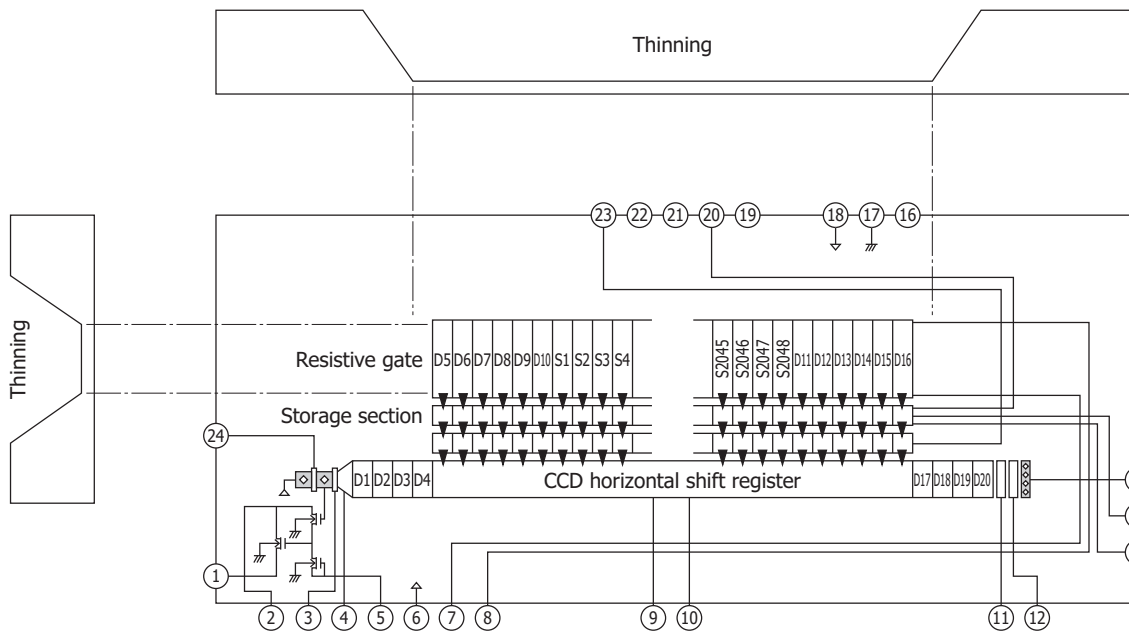
\*15: Spectral response with quartz glass is decreased according to the spectral transmittance characteristic of window material.

**Window material**

Type No.	Window material
S11155-2048	Quartz glass*16 (option: window-less)
S11156-2048	

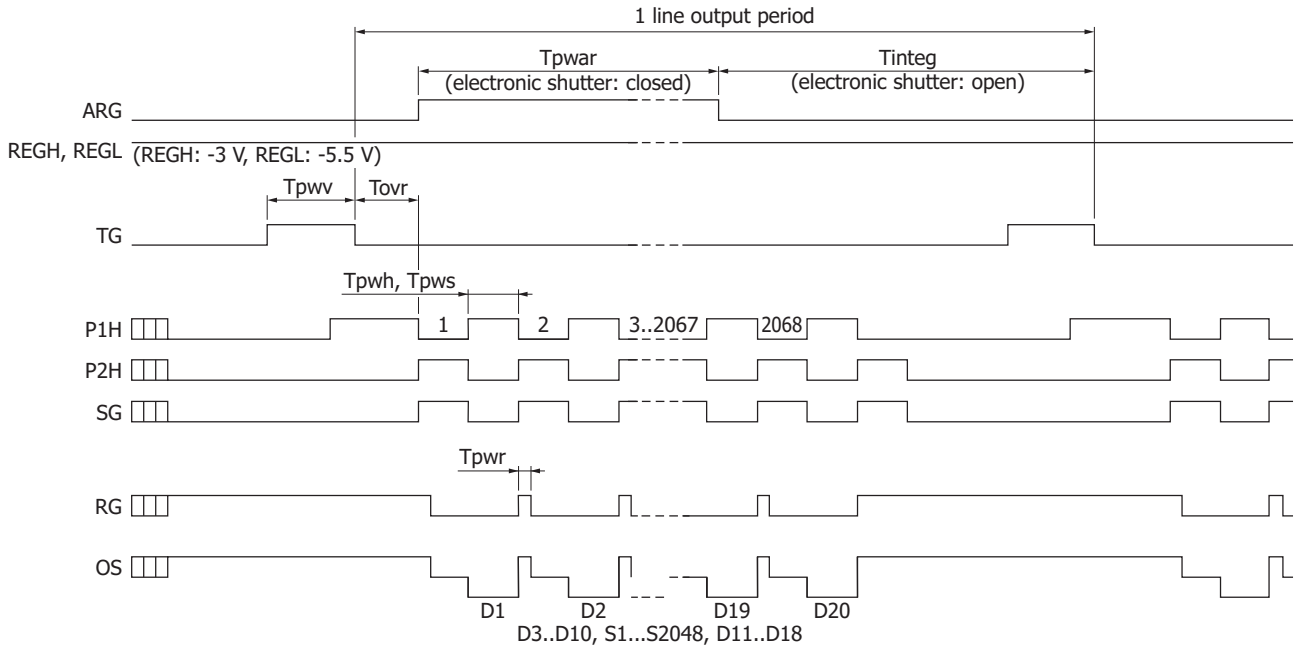
\*16: Resin sealing

**Device structure (conceptual drawing of top view in dimensional outline)**



**Timing chart**

Non-MPP operation

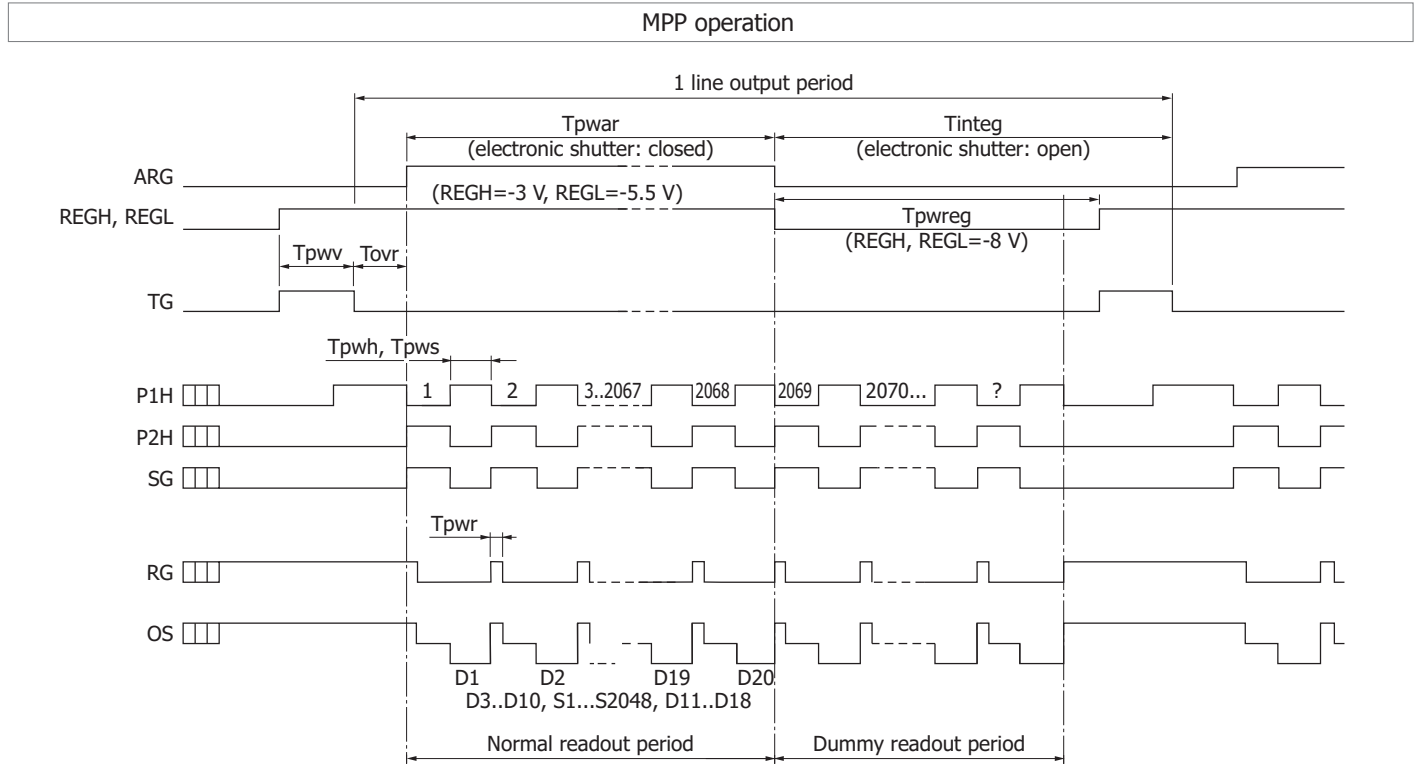


KMPDC0340EB

Parameter		Symbol	Min.	Typ.	Max.	Unit
ARG	Pulse width	Tpwar	1	-	-	μs
	Rise and fall times	Tprar, Tpfar	200	-	-	ns
TG	Pulse width	Tpww	30	-	-	μs
	Rise and fall time	Tprv, Tpfv	20	-	-	ns
P1H, P2H*17	Pulse width	Tpwh	50	100	-	ns
	Rise and fall time	Tprh, Tpfh	10	-	-	ns
	Duty ratio	-	40	50	60	%
SG	Pulse width	Tpws	50	100	-	ns
	Rise and fall time	Tprs, Tpfs	10	-	-	ns
	Duty ratio	-	40	50	60	%
RG	Pulse width	Tpwr	5	15	-	ns
	Rise and fall time	Tprr, Tpfr	5	-	-	ns
TG - P1H	Overlap time	Tovr	1	2	-	μs
Integration time		Tinteg	30	-	-	μs

\*17: Symmetrical clock pulses should be overlapped at 50% of maximum amplitude.

Timing chart



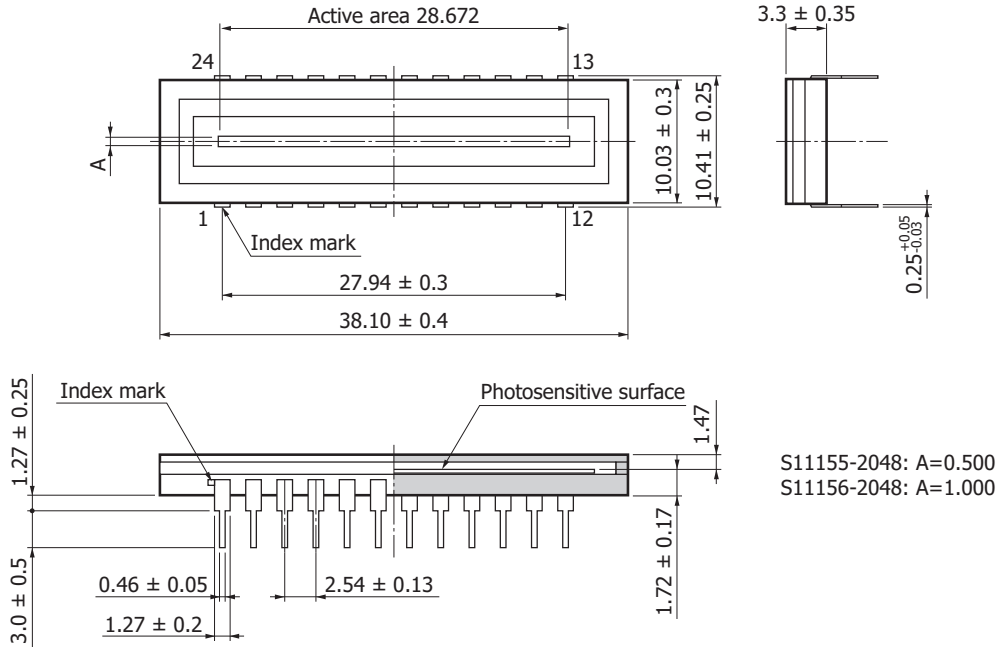
KMPD0347EC

Parameter		Symbol	Min.	Typ.	Max.	Unit
ARG	Pulse width	$T_{pwar}$	*18	-	-	$\mu$ s
	Rise and fall times	$T_{prar}, T_{pfar}$	200	-	-	ns
REGH, REGL	Pulse width	$T_{pwreg}$	-	$T_{integ} - T_{pww}$	-	$\mu$ s
	Rise and fall times	$T_{prreg}, T_{pfreg}$	100	-	-	ns
TG	Pulse width	$T_{pww}$	30	-	-	$\mu$ s
	Rise and fall times	$T_{prv}, T_{pfv}$	20	-	-	ns
P1H, P2H*19	Pulse width	$T_{pwh}$	50	100	-	ns
	Rise and fall times	$T_{prh}, T_{pfh}$	10	-	-	ns
	Duty ratio	-	40	50	60	%
SG	Pulse width	$T_{pws}$	50	100	-	ns
	Rise and fall times	$T_{prs}, T_{pfs}$	10	-	-	ns
	Duty ratio	-	40	50	60	%
RG	Pulse width	$T_{pwr}$	5	15	-	ns
	Rise and fall times	$T_{pr}, T_{pf}$	5	-	-	ns
TG - P1H	Overlap time	$T_{ovr}$	1	2	-	$\mu$ s
Integration time		$T_{integ}$	30	-	-	$\mu$ s

\*18: The Min. value of  $T_{pwar}$  is equal to the normal readout period.

\*19: Symmetrical clock pulses should be overlapped at 50% of maximum amplitude.

**Dimensional outline (unit: mm)**



KMPDA0262EB

**Pin connections**

Pin no.	Symbol	Function	Remark (standard operation)
1	OS	Output transistor source	$R_L=2.2\text{ k}\Omega$
2	OD	Output transistor drain	+15 V
3	OG	Output gate	+5 V
4	SG	Summing gate	Same pulse as P2H
5	Vret	Output amplifier return	+1 V
6	RD	Reset drain	+15 V
7	REGL	Resistive gate (low)	-5.5 V (Non-MPP operation)
8	REGH	Resistive gate (high)	-3 V (Non-MPP operation)
9	P2H	CCD horizontal register clock-2	
10	P1H	CCD horizontal register clock-1	
11	IG2H	Test point (horizontal input gate-2)	-8 V
12	IG1H	Test point (horizontal input gate-1)	-8 V
13	ARG	All reset gate	
14	ARD	All reset drain	+12 V
15	ISH	Test point (horizontal input source)	Connect to RD
16	-		
17	SS	Substrate	GND
18	RD	Reset drain	+15 V
19	-		
20	STG	Storage gate	0 V
21	-		
22	-		
23	TG	Transfer gate	
24	RG	Reset gate	

**Related information**

[http://jp.hamamatsu.com/sp/ssd/CCD\\_e.html](http://jp.hamamatsu.com/sp/ssd/CCD_e.html)

- Characteristics and use of resistive gate type CCD linear image sensors with electronic shutter

Driver circuits for CCD linear image sensor (S11155-2048, S11156-2048) C11165 [sold separately]

The C11165 is a driver circuit designed for HAMAMATSU CCD linear image sensors S11155-2048, S11156-2048. The C11165 can be used in spectrometer when combined with the CCD linear image sensor.

**Features**

- Built-in 16-bit A/D converter
- Interface of computer: USB 2.0
- Operates by DC+5 V



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